

Direct and Remote Plasma Assisted CVD at Atmospheric Pressure for the Preparation of Oxide Thin Films



Bewertung: Noch nicht bewertet

Preis

ermäßigter Preis 2,52 €

2,70 €

Netto-Preis: 2,52 €

Enthaltene MwSt.: 0,18 €

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Beschreibung In this paper the preparation of silicon and titanium oxide thin films using an atmospheric pressure plasma process will be reported. To obtain these oxide films hexamethyldisiloxane and titanium tetraisopropoxide were used as precursor materials. Based on the different chemical reaction mechanisms the film deposition processes were carried out in the direct as well as in the remote PACVD mode. The deposition parameters were varied and the influence on different film properties was studied. The deposited oxide films were characterised by profilometry, ellipsometry, SEM, UV-VIS-NIR-transmission measurements, FT-IR spectroscopy and contact angle measurements. Additionally, first results will be presented concerning the creation of composite films using a combination of plasma and liquid dye nebulization technique.